

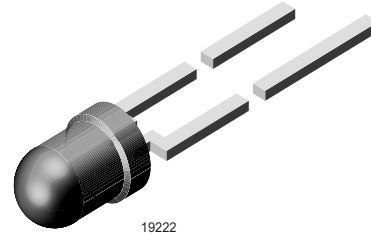
High Intensity LED in \varnothing 3 mm Tinted Diffused Package

Description

This device has been designed to meet the increasing demand for AlInGaP technology.

It is housed in a 3 mm clear plastic package. The wide viewing angle of these devices provides a high on-off contrast.

All packing units are categorized in luminous intensity groups. That allows users to assemble LEDs with uniform appearance.



Features

- AlInGaP technology
- Standard \varnothing 3 mm (T-1) package
- Small mechanical tolerances
- Suitable for DC and high peak current
- Very wide viewing angle
- Luminous intensity categorized
- Lead-free device

Applications

Status lights
 OFF / ON indicator
 Background illumination
 Readout lights
 Maintenance lights
 Legend light

Parts Table

Part	Color, Luminous Intensity	Angle of Half Intensity ($\pm\phi$)	Technology
TLHK4600	Red, $I_V > 6.3$ mcd	60 °	AlInGaP on GaAs

Absolute Maximum Ratings

$T_{amb} = 25$ °C, unless otherwise specified

TLHK4600

Parameter	Test condition	Symbol	Value	Unit
Reverse voltage		V_R	5	V
DC Forward current	$T_{amb} \leq 60$ °C	I_F	30	mA
Surge forward current	$t_p \leq 10$ μ s	I_{FSM}	0.1	A
Power dissipation	$T_{amb} \leq 60$ °C	P_V	80	mW
Junction temperature		T_j	100	°C
Operating temperature range		T_{amb}	- 40 to + 100	°C
Storage temperature range		T_{stg}	- 55 to + 100	°C
Soldering temperature	$t \leq 5$ s, 2 mm from body	T_{sd}	260	°C
Thermal resistance junction/ambient		R_{thJA}	400	K/W

Optical and Electrical Characteristics

$T_{amb} = 25\text{ }^{\circ}\text{C}$, unless otherwise specified

Red

TLHK4600

Parameter	Test condition	Symbol	Min	Typ.	Max	Unit
Luminous intensity ¹⁾	$I_F = 10\text{ mA}$	I_V	6.3	15		mcd
Dominant wavelength	$I_F = 10\text{ mA}$	λ_d		630		nm
Peak wavelength	$I_F = 10\text{ mA}$	λ_p		643		nm
Angle of half intensity	$I_F = 10\text{ mA}$	ϕ		± 60		deg
Forward voltage	$I_F = 20\text{ mA}$	V_F		1.9	2.6	V
Junction capacitance	$V_R = 0, f = 1\text{ MHz}$	C_j		15		pF
Reverse voltage	$I_R = 10\text{ }\mu\text{A}$	V_R	5			V

¹⁾ in one Packing Unit $I_{Vmin}/I_{Vmax} \leq 0.5$

Typical Characteristics ($T_{amb} = 25\text{ }^{\circ}\text{C}$ unless otherwise specified)

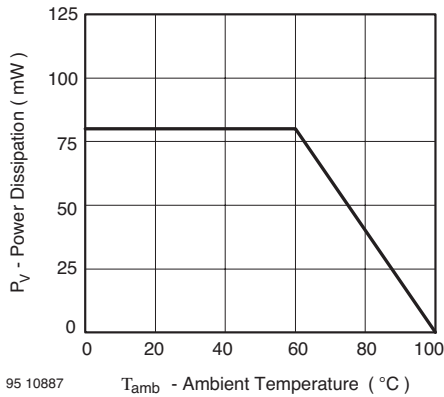


Figure 1. Power Dissipation vs. Ambient Temperature

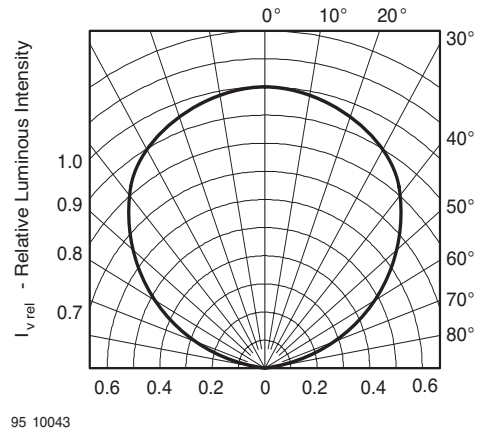


Figure 3. Rel. Luminous Intensity vs. Angular Displacement

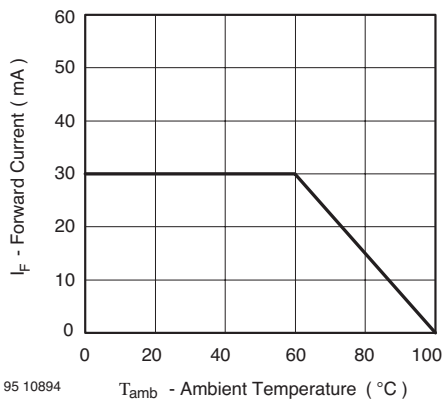


Figure 2. Forward Current vs. Ambient Temperature for InGaN

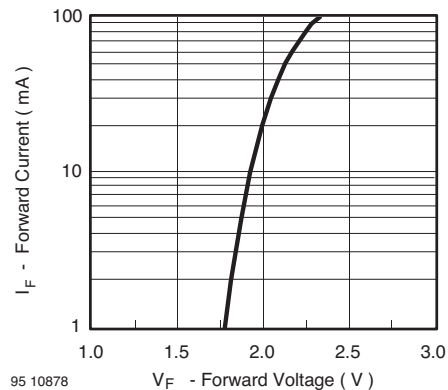


Figure 4. Forward Current vs. Forward Voltage

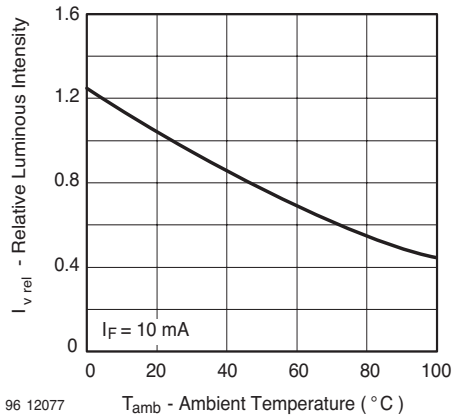


Figure 5. Rel. Luminous Intensity vs. Ambient Temperature

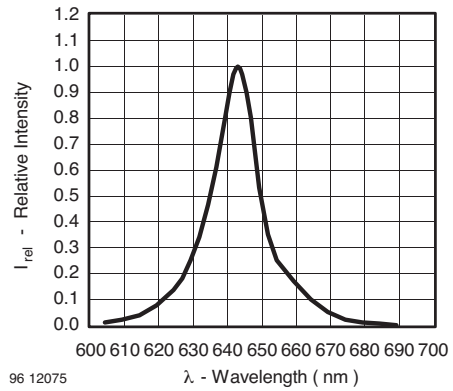


Figure 8. Relative Intensity vs. Wavelength

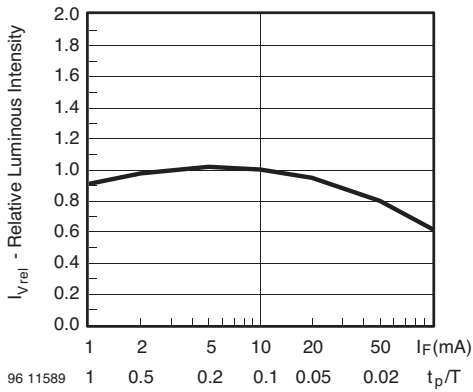


Figure 6. Rel. Lumin. Intensity vs. Forw. Current/Duty Cycle

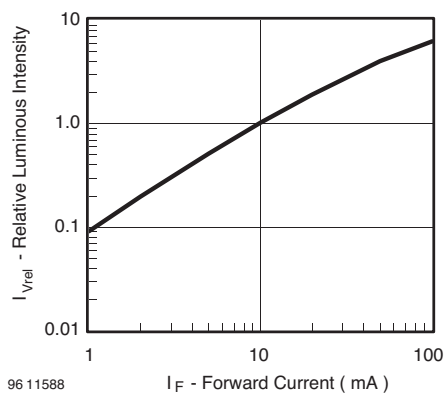


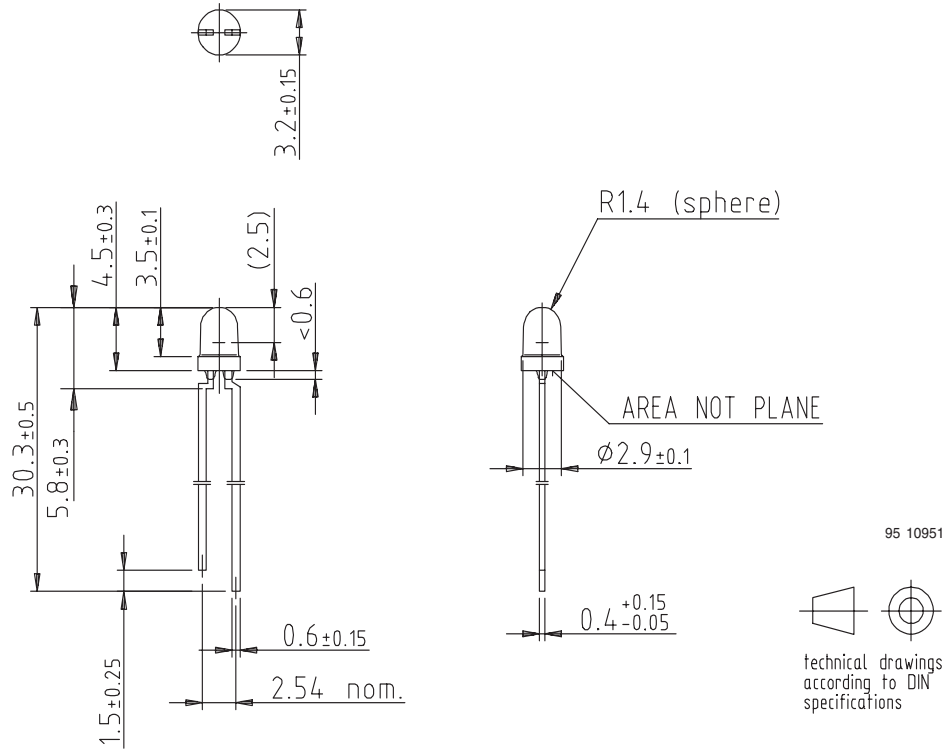
Figure 7. Relative Luminous Intensity vs. Forward Current

TLHK4600

Vishay Semiconductors



Package Dimensions in mm





Ozone Depleting Substances Policy Statement

It is the policy of **Vishay Semiconductor GmbH** to

1. Meet all present and future national and international statutory requirements.
2. Regularly and continuously improve the performance of our products, processes, distribution and operating systems with respect to their impact on the health and safety of our employees and the public, as well as their impact on the environment.

It is particular concern to control or eliminate releases of those substances into the atmosphere which are known as ozone depleting substances (ODSs).

The Montreal Protocol (1987) and its London Amendments (1990) intend to severely restrict the use of ODSs and forbid their use within the next ten years. Various national and international initiatives are pressing for an earlier ban on these substances.

Vishay Semiconductor GmbH has been able to use its policy of continuous improvements to eliminate the use of ODSs listed in the following documents.

1. Annex A, B and list of transitional substances of the Montreal Protocol and the London Amendments respectively
2. Class I and II ozone depleting substances in the Clean Air Act Amendments of 1990 by the Environmental Protection Agency (EPA) in the USA
3. Council Decision 88/540/EEC and 91/690/EEC Annex A, B and C (transitional substances) respectively.

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На всех этапах разработки и производства наши партнеры могут получить квалифицированную поддержку опытных инженеров.

Система менеджмента качества компании отвечает требованиям в соответствии с ГОСТ Р ИСО 9001, ГОСТ РВ 0015-002 и ЭС РД 009

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